R1LV1616HBG-I Series

Wide Temperature Range Version
16 M SRAM (1-Mword × 16-bit)

REJ03C0263-0100
Rev.1.00
Sep.21.2005

Description

The R1LV1616HBG-I Series is 16-Mbit static RAM organized 1-Mword × 16-bit. R1LV1616HBG-I Series has realized higher density, higher performance and low power consumption by employing CMOS process technology (6-transistor memory cell). It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is packaged in 48-ball plastic FBGA for high density surface mounting.

Features

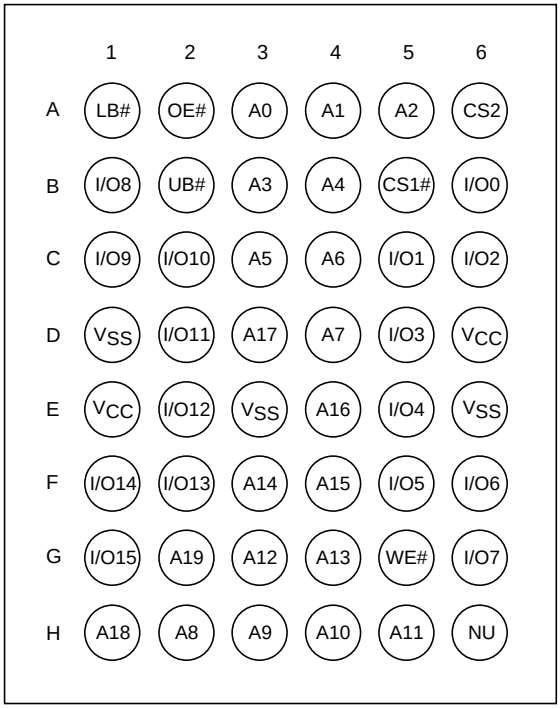
- Single 3.0 V supply: 2.7 V to 3.6 V
- Fast access time: 45/55 ns (max)
- Power dissipation:
  - Active: 9 mW/MHz (typ)
  - Standby: 1.5 µW (typ)
- Completely static memory.
  - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
  - Three state output
- Battery backup operation.
  - 2 chip selection for battery backup
- Temperature range: –40 to +85°C

Ordering Information

Type No.	Access time	Package
R1LV1616HBG-4SI	45 ns	48-ball plastic FBGA with 0.75 mm ball pitch
R1LV1616HBG-5SI	55 ns	PTBG0048HF (48FHJ)

Pin Arrangement

48-ball FBGA



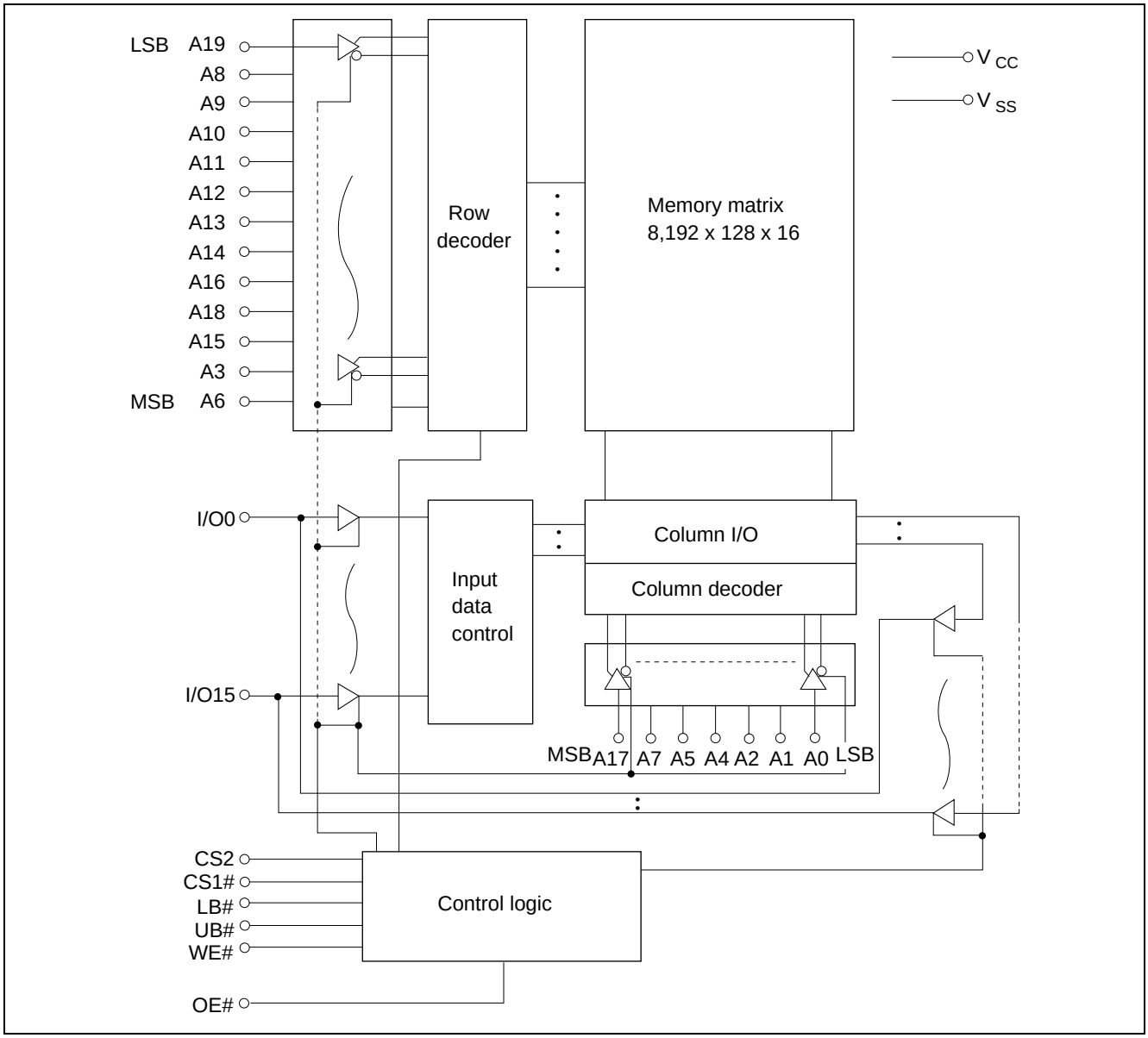
(Top view)

Pin Description

Pin name	Function
A0 to A19	Address input
I/O0 to I/O15	Data input/output
CS1# ($\overline{CS1}$)	Chip select 1
CS2	Chip select 2
WE# ($\overline{WE}$)	Write enable
OE# ($\overline{OE}$)	Output enable
LB# ($\overline{LB}$)	Lower byte select
UB# ($\overline{UB}$)	Upper byte select
V_{CC}	Power supply
V_{SS}	Ground
NU*[1]	Not used (test mode pin)

Note: 1. This pin should be connected to a ground (V_{SS}), or not be connected (open).

Block Diagram



Operation Table

CS1#	CS2	WE#	OE#	UB#	LB#	I/O0 to I/O7	I/O8 to I/O15	Operation
H	×	×	×	×	×	High-Z	High-Z	Standby
×	L	×	×	×	×	High-Z	High-Z	Standby
×	×	×	×	H	H	High-Z	High-Z	Standby
L	H	H	L	L	L	Dout	Dout	Read
L	H	H	L	H	L	Dout	High-Z	Lower byte read
L	H	H	L	L	H	High-Z	Dout	Upper byte read
L	H	L	×	L	L	Din	Din	Write
L	H	L	×	H	L	Din	High-Z	Lower byte write
L	H	L	×	L	H	High-Z	Din	Upper byte write
L	H	H	H	×	×	High-Z	High-Z	Output disable

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{CC}	–0.5 to +4.6	V
Terminal voltage on any pin relative to V_{SS}	V_T	–0.5*[1] to V_{CC} + 0.3*[2]	V
Power dissipation	P_T	1.0	W
Storage temperature range	Tstg	–55 to +125	°C
Storage temperature range under bias	Tbias	–40 to +85	°C

Notes: 1. V_T min: –2.0 V for pulse half-width ≤ 10 ns.
2. Maximum voltage is +4.6 V.

DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	V_{CC}	2.7	3.0	3.6	V	
	V_{SS}	0	0	0	V	
Input high voltage	V_{IH}	2.2	—	V_{CC} + 0.3	V	
Input low voltage	V_{IL}	–0.3	—	0.6	V	1
Ambient temperature range	Ta	–40	—	+85	°C	

Note: 1. V_{IL} min: –2.0 V for pulse half-width ≤ 10 ns.

DC Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input leakage current	$\|I_{LI}\|$	—	—	1	µA	Vin = V_{SS} to V_{CC}
Output leakage current	$\|I_{LO}\|$	—	—	1	µA	CS1# = V_{IH} or CS2 = V_{IL} or OE# = V_{IH} or WE# = V_{IL} or LB# = UB# = V_{IH}, $V_{I/O}$ = V_{SS} to V_{CC}
Operating current	I_{CC}	—	—	20	mA	CS1# = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/ V_{IL}, $I_{I/O}$ = 0 mA
Average operating current	I_{CC1} (READ)	—	22*[1]	35	mA	Min. cycle, duty = 100%, $I_{I/O}$ = 0 mA, CS1# = V_{IL}, CS2 = V_{IH}, WE# = V_{IH}, Others = V_{IH}/V_{IL}
	I_{CC1}	—	30*[1]	50	mA	Min. cycle, duty = 100%, $I_{I/O}$ = 0 mA, CS1# = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/V_{IL}
	I_{CC2} (READ)	—	3*[1]	8	mA	Cycle time = 70 ns, duty = 100%, $I_{I/O}$ = 0 mA, CS1# = V_{IL}, CS2 = V_{IH}, WE# = V_{IH}, Others = V_{IH}/V_{IL} Address increment scan or decrement scan
	I_{CC2}	—	20*[1]	30	mA	Cycle time = 70 ns, duty = 100%, $I_{I/O}$ = 0 mA, CS1# = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/V_{IL} Address increment scan or decrement scan
	I_{CC3}	—	3*[1]	8	mA	Cycle time = 1 µs, duty = 100%, $I_{I/O}$ = 0 mA, CS1# ≤ 0.2 V, CS2 ≥ V_{CC} – 0.2 V V_{IH} ≥ V_{CC} – 0.2 V, V_{IL} ≤ 0.2 V
Standby current	I_{SB}	—	0.1*[1]	0.5	mA	CS2 = V_{IL}
	I_{SB1}	—	0.5*[1]	8	µA	0 V ≤ Vin (1) 0 V ≤ CS2 ≤ 0.2 V or (2) CS1# ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V or (3) LB# = UB# ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V, CS1# ≤ 0.2 V Average value
Output high voltage	V_{OH}	2.4	—	—	V	I_{OH} = –1 mA
	V_{OH}	V_{CC} – 0.2	—	—	V	I_{OH} = –100 µA
Output low voltage	V_{OL}	—	—	0.4	V	I_{OL} = 2 mA
	V_{OL}	—	—	0.2	V	I_{OL} = 100 µA

Notes: 1. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and not guaranteed.

Capacitance

(Ta = +25°C, f = 1.0 MHz)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	Note
Input capacitance	Cin	—	—	8	pF	Vin = 0 V	1
Input/output capacitance	$C_{I/O}$	—	—	10	pF	$V_{I/O}$ = 0 V	1

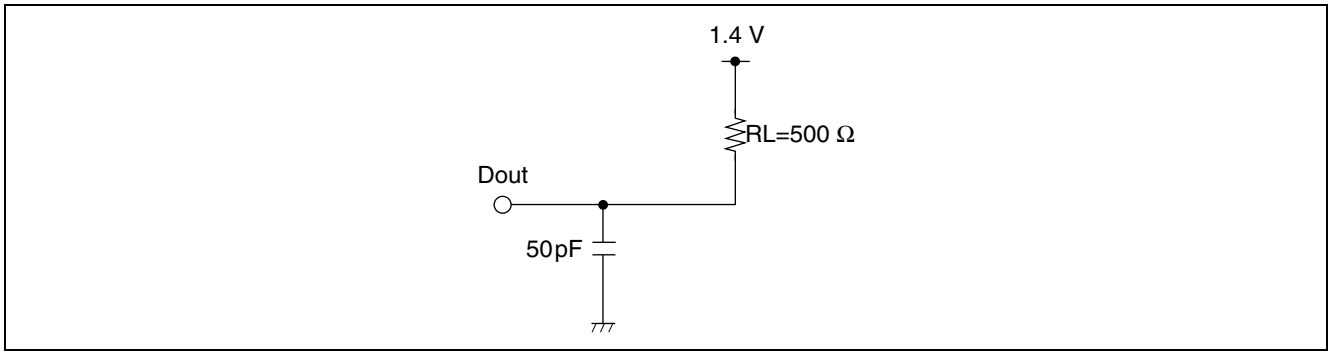
Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics

(Ta = –40 to +85°C, V_{CC} = 2.7 V to 3.6 V)

Test Conditions

- Input pulse levels: V_{IL} = 0.4 V, V_{IH} = 2.4 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.4 V
- Output load: See figures (Including scope and jig)



Read Cycle

Parameter	Symbol	R1LV1616HBG-I				Unit	Notes
		-4SI		-5SI			
		Min	Max	Min	Max		
Read cycle time	t_{RC}	45	—	55	—	ns	
Address access time	t_{AA}	—	45	—	55	ns	
Chip select access time	t_{ACS1}	—	45	—	55	ns	
	t_{ACS2}	—	45	—	55	ns	
Output enable to output valid	t_{OE}	—	30	—	35	ns	
Output hold from address change	t_{OH}	10	—	10	—	ns	
LB#, UB# access time	t_{BA}	—	45	—	55	ns	
Chip select to output in low-Z	t_{CLZ1}	10	—	10	—	ns	2, 3
	t_{CLZ2}	10	—	10	—	ns	2, 3
LB#, UB# enable to low-Z	t_{BLZ}	5	—	5	—	ns	2, 3
Output enable to output in low-Z	t_{OLZ}	5	—	5	—	ns	2, 3
Chip deselect to output in high-Z	t_{CHZ1}	0	20	0	20	ns	1, 2, 3
	t_{CHZ2}	0	20	0	20	ns	1, 2, 3
LB#, UB# disable to high-Z	t_{BHZ}	0	15	0	20	ns	1, 2, 3
Output disable to output in high-Z	t_{OHZ}	0	15	0	20	ns	1, 2, 3

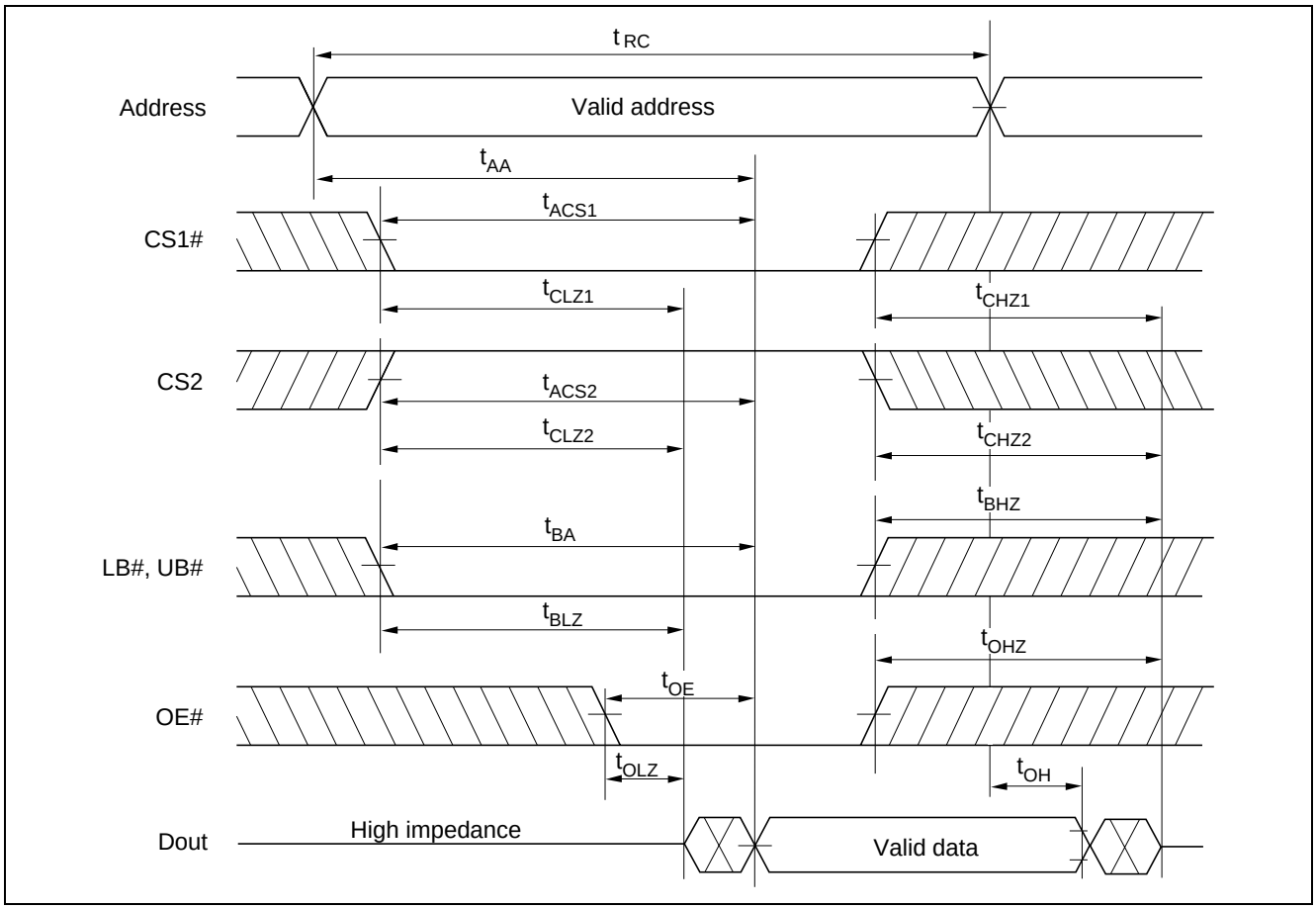
Write Cycle

Parameter	Symbol	R1LV1616HBG-I				Unit	Notes
		-4SI		-5SI			
		Min	Max	Min	Max		
Write cycle time	t_{WC}	45	—	55	—	ns	
Address valid to end of write	t_{AW}	45	—	50	—	ns	
Chip selection to end of write	t_{CW}	45	—	50	—	ns	5
Write pulse width	t_{WP}	35	—	40	—	ns	4
LB#, UB# valid to end of write	t_{BW}	45	—	50	—	ns	
Address setup time	t_{AS}	0	—	0	—	ns	6
Write recovery time	t_{WR}	0	—	0	—	ns	7
Data to write time overlap	t_{DW}	25	—	25	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	ns	
Output active from end of write	t_{OW}	5	—	5	—	ns	2
Output disable to output in high-Z	t_{OHZ}	0	15	0	20	ns	1, 2
Write to output in high-Z	t_{WHZ}	0	15	0	20	ns	1, 2

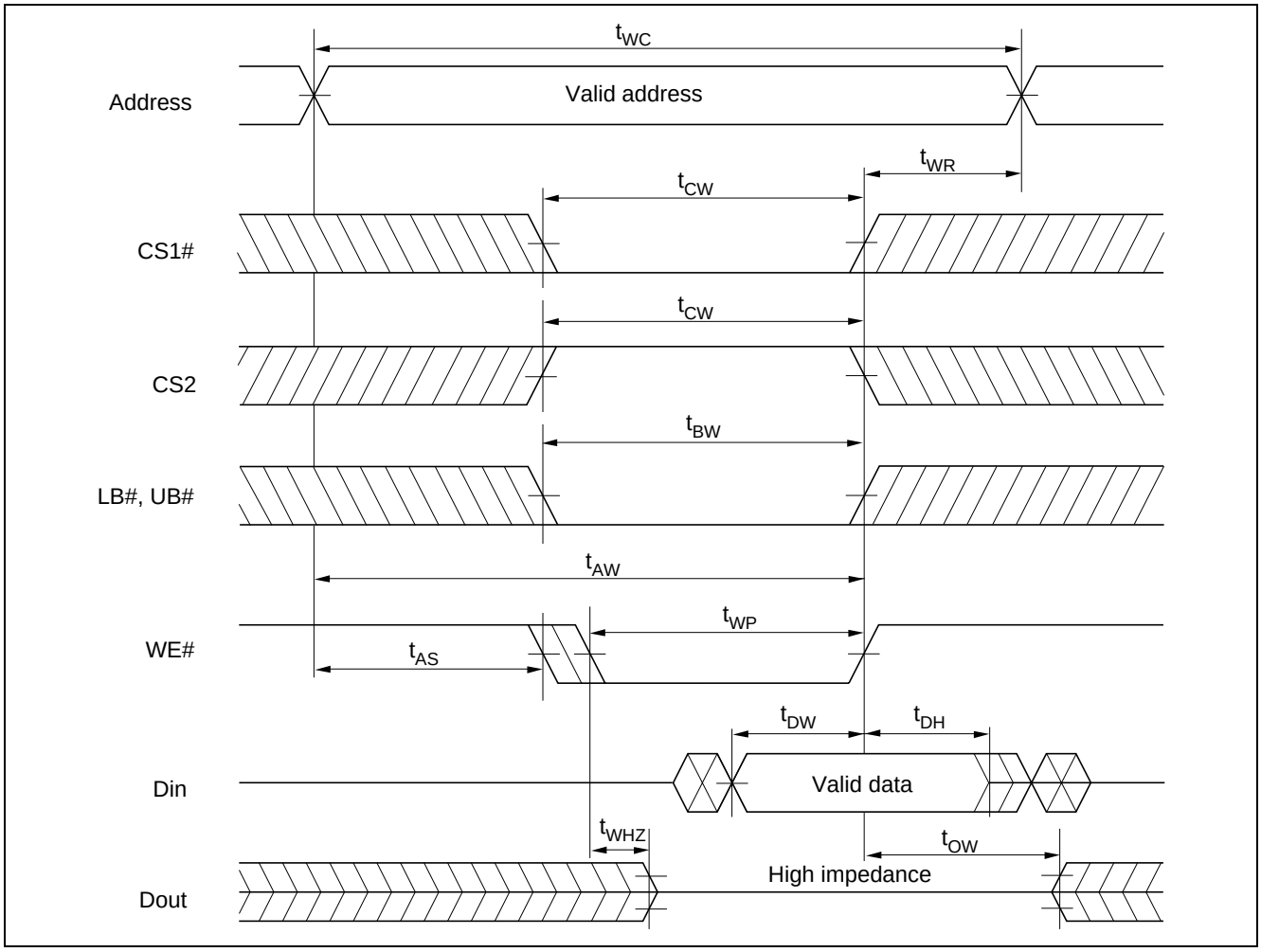
Notes:
1. t_{CHZ}, t_{OHZ}, t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
2. This parameter is sampled and not 100% tested.
3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.
4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#. A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low. A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. t_{WP} is measured from the beginning of write to the end of write.
5. t_{CW} is measured from the later of CS1# going low or CS2 going high to the end of write.
6. t_{AS} is measured from the address valid to the beginning of write.
7. t_{WR} is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.

Timing Waveform

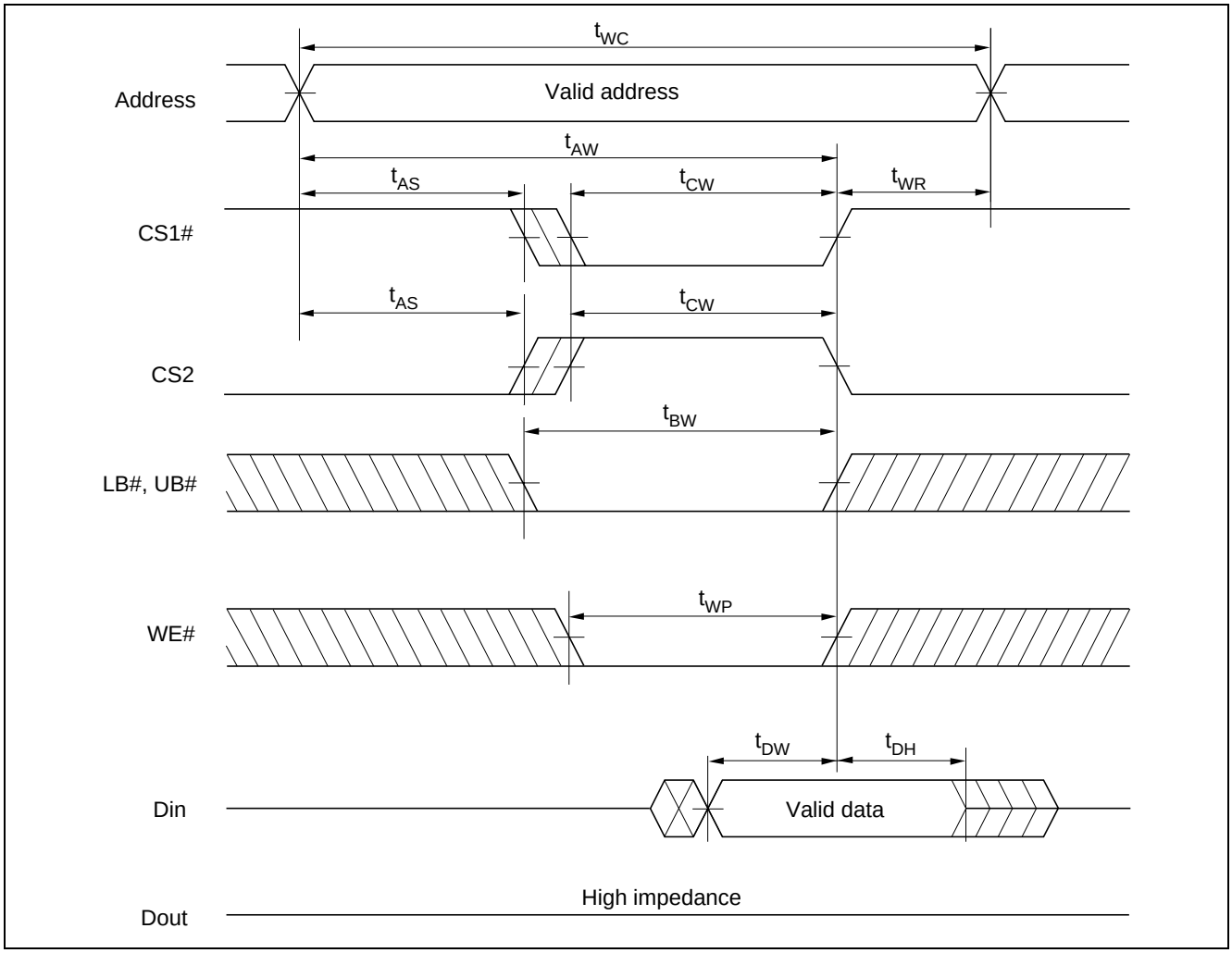
Read Cycle



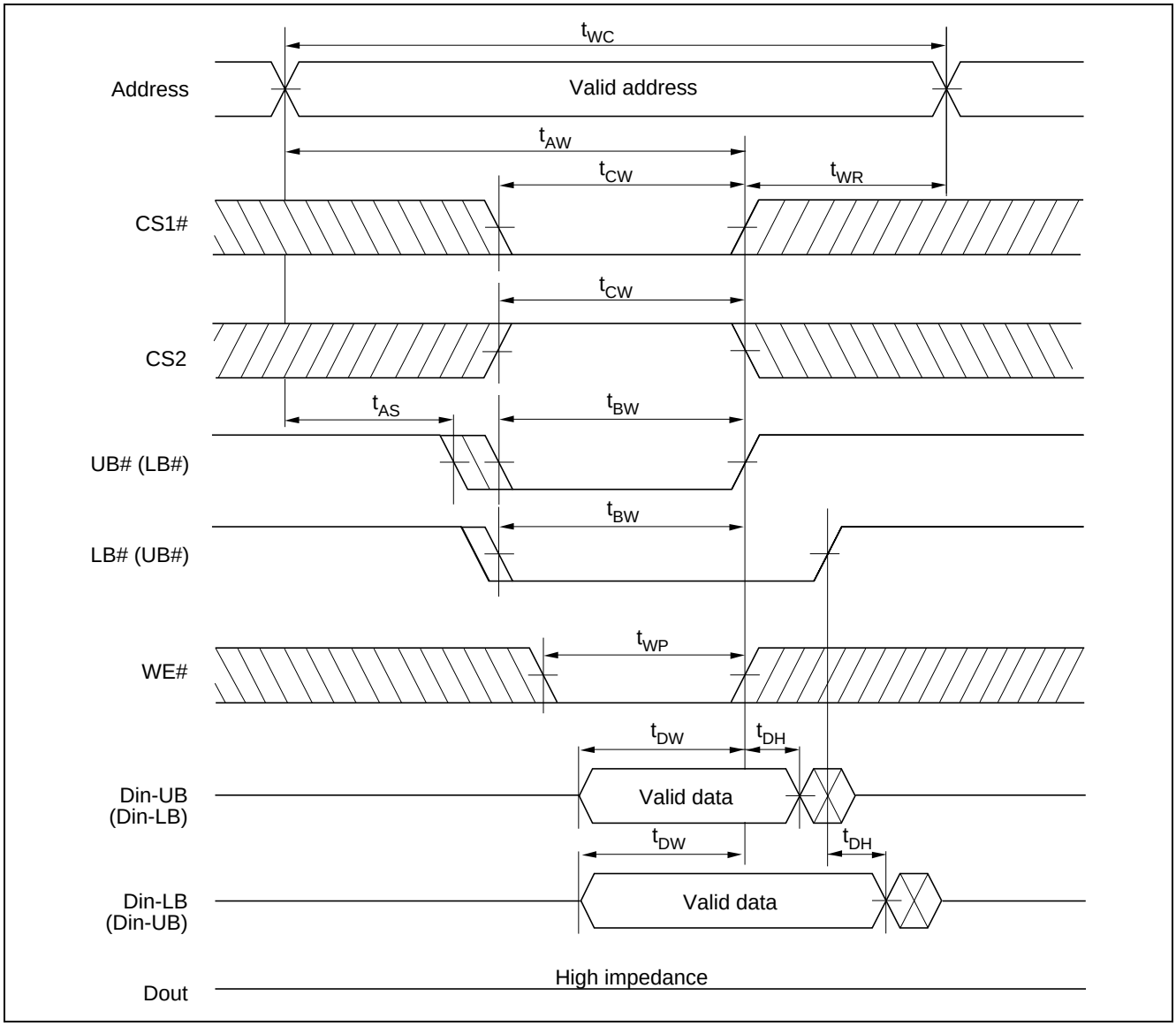
Write Cycle (1) (WE# Clock)



Write Cycle (2) (CS1#, CS2 Clock, OE# = V_{IH})



Write Cycle (3) (LB#, UB# Clock, OE# = V_{IH})



Low V_{CC} Data Retention Characteristics

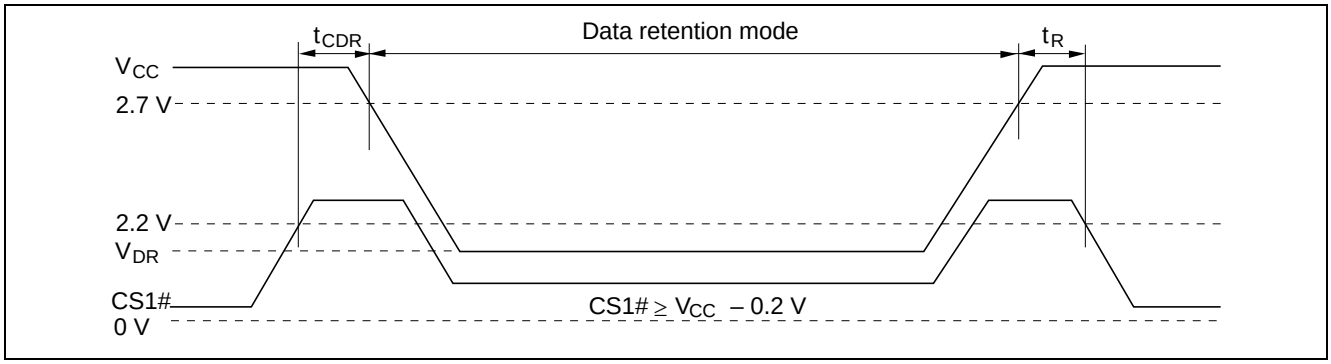
(Ta = –40 to +85°C)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions*[2]
V_{CC} for data retention	V_{DR}	1.5	—	3.6	V	Vin ≥ 0 V (1) 0 V ≤ CS2 ≤ 0.2 V or (2) CS2 ≥ V_{CC} – 0.2 V, CS1# ≥ V_{CC} – 0.2 V or (3) LB# = UB# ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V, CS1# ≤ 0.2 V
Data retention current	I_{CCDR}	—	0.5*[1]	8	µA	V_{CC} = 3.0 V, Vin ≥ 0 V (1) 0 V ≤ CS2 ≤ 0.2 V or (2) CS2 ≥ V_{CC} – 0.2 V, CS1# ≥ V_{CC} – 0.2 V or (3) LB# = UB# ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V, CS1# ≤ 0.2 V Average value
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveforms
Operation recovery time	t_R	5	—	—	ms	

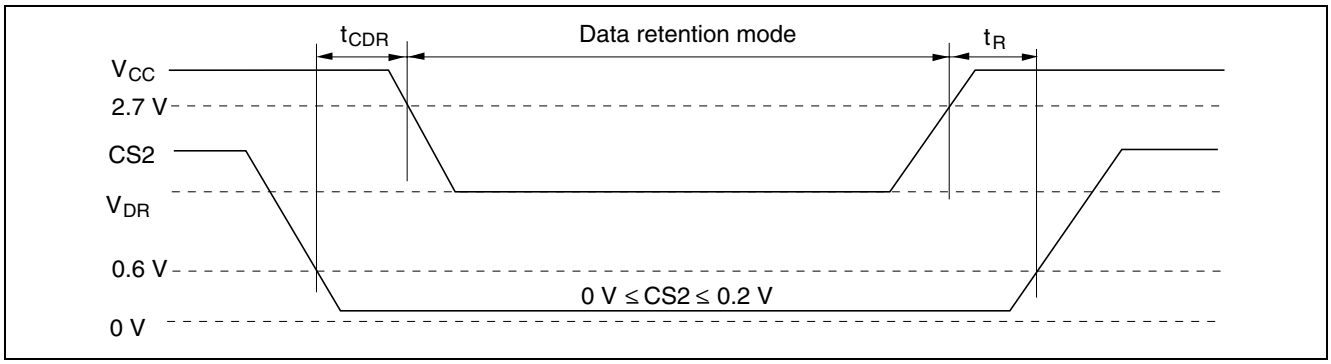
Notes: 1. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and not guaranteed.

2. CS2 controls address buffer, WE# buffer, CS1# buffer, OE# buffer, LB#, UB# buffer and Din buffer. If CS2 controls data retention mode, Vin levels (address, WE#, OE#, CS1#, LB#, UB#, I/O) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be CS2 ≥ V_{CC} – 0.2 V or 0 V ≤ CS2 ≤ 0.2 V. The other input levels (address, WE#, OE#, LB#, UB#, I/O) can be in the high impedance state.

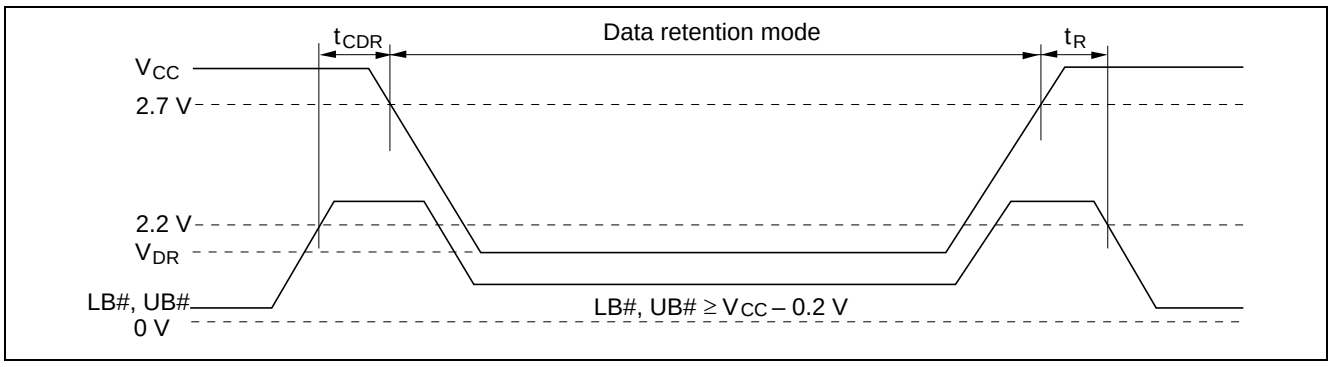
Low V_{CC} Data Retention Timing Waveform (1) (CS1# Controlled)



Low V_{CC} Data Retention Timing Waveform (2) (CS2 Controlled)



Low V_{CC} Data Retention Timing Waveform (3) (LB#, UB# Controlled)



Revision History	R1LV1616HBG-I Series Data Sheet

Rev.	Date	Contents of Modification	
		Page	Description
0.01	Apr. 29. 2005	—	Initial issue
1.00	Sep. 21. 2005	—	Deletion of Preliminary

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.
450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.
Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510

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